Supporting Information

High Performance Oxygen-bridged N-shaped Semiconductors with Stabilized Crystal Phase and Blue Luminescence

Chikahiko Mitsui,^{*a*} Yuji Tanaka,^{*b*} Shota Tanaka,^{*b*} Masakazu Yamagishi,^{*a*} Katsumasa Nakahara,^{*c*} Masafumi Yano,^{*b*} Hiroyasu Sato,^{*d*} Akihito Yamano,^{*d*} Hiroyuki Matsui,^{*a*} Jun Takeya,^{*a,c*} and Toshihiro Okamoto^{**a,c,e*}

^a Department of Advanced Materials Science, Graduate School of Frontier Sciences, The University of Tokyo, 5-1-5 Kashiwanoha, Kashiwa, Chiba 277-8561, Japan.

^bGraduate School of Science and Engineering, Kansai University, 3-3-35 Yamate-cho, Suita, Osaka 564-8680, Japan.

^c The Institute of Scientific and Industrial Research (ISIR), Osaka University, 8-1 Mihogaoka, Ibaraki, Osaka 567-0047, Japan.

^dRigaku Corp., 3-9-12 Matsubara-cho, Akishima, Tokyo 196-8666, Japan.

^e PRESTO, Japan Society and Technology Agency (JST), 4-1-8 Honcho, Kawaguchi, Saitama 332-0012, Japan.

Contents

- 1. Synthesis
- 2. Absorption Spectra in Evaporated Thin Film
- 3. Fluorescent Spectra
- 4. Ionization Potentials
- 5. Thermal Analyses
- 6. Single-Crystal Analyses
- 7. Theoretical Calculations
- 8. OFET Device Fabrication and Evaluation Procedure
- 9. X-ray-diffraction Measurements for Solution-crystallized Thin Film
- 10. Photograph of solution-crystallized thin film of C_{10} -DNBDF-NV
- 11. References

1. Synthesis

1.1 Materials

Reagents and Starting Materials

1.0 M boron tribromide in dichloromethane and PdCl₂(dppp) was purchased from TCI. 1,4-Dibromo-2,5-dimethoxybenzene and zinc chloride (99.999% trace metals basis) were purchased from Sigma-Aldrich Inc. n-BuLi and 1,2-dichlorobenzene were purchased from Kanto chemicals. Zeolite HSZ-360 was purchased from TOSOH Corp. All anhydrous solvents were purchased from Kanto chemicals. procedure.^[1] 2-Decyl-6-methoxynaphthalene reported was prepared by the 2,5-Bis(3-hydroxynaphthalen-2-yl)benzene-1,4-diol and 2,5-bis(6-decyl-3-hydroxynaphthalen-2-yl)benzene-1,4-diol were synthesized according to the previously reported procedure.^[2]

1.2 Methods

General for Synthesis and Characterization

All the reactions were carried out under an atmosphere of nitrogen. Air- or moisture-sensitive liquids and solutions were transferred via a syringe or a Teflon cannula. Analytical thin-layer chromatography (TLC) was performed on glass plates with 0.25 mm 230-400 mesh silica gel containing a fluorescent indicator (Merck Silica gel 60 F254). TLC plates were visualized by either exposure to ultraviolet lamp (254 nm and 365 nm) or by dipping with 10% phosphomolybdic acid in ethanol and then heating on a hot plate. Flash column chromatography was performed on Kanto silica gel 60. Open column chromatography was performed on Wakogel C-200 (75-150 µm). All NMR spectra were recorded on a JEOL ECA600 and JEOL ECS400 spectrometers. Chemical shifts are reported in parts per million (ppm, δ scale) from residual protons in the deuterated solvent for ¹H NMR (δ 7.26 ppm for chloroform, δ 5.93 ppm for 1,1,2,2-tetrachloroethane, and δ 1.73 ppm for tetrahydrofuran) and from the solvent carbon for ¹³C NMR (δ 77.16 ppm for chloroform and δ 25.5 ppm for tetrahydrofuran). The data were presented in the following format: chemical shift, multiplicity (s = singlet, d = doublet, t = triplet, m = multiplet), coupling constant in Hertz (Hz), signal area integration in natural numbers, assignment (italic). Mass spectra were measured on a JEOL JMS-T100LC APCI/ESI mass spectrometer. Melting points and elemental

analyses were collected on a Mettler Toledo MP70 Melting Point System and J-Science Lab JM10 MICRO CORDER, respectively.

1.3 Experimental Section





To a solution of 2-decyl-6-methoxynaphthalene (10.3 g, 34.5 mmol, 2.4 mol amt. for 1,4-dibromo-2,5-dimethoxyibenzene) in THF (138 mL) was added 1.65 M n-BuLi in hexane (23.0 mL, 38.0 mmol, 1.1 mol amt. for 2-decyl-6-methoxynaphthalene) at 0 °C. After stirring at 0 °C for 3 h, 1.0 M zinc chloride in THF (38.0 mL, 38.0 mmol, 1.1 mol amt. for 2-decyl-6-methoxynaphthalene) was added at 0 °C and the resultant mixture was stirred at room temperature for 1 h. To the resulting pale yellow solution were added 1,4-dibromo-2,5-dimethoxybenzene (4.26 g, 14.4 mmol) and PdCl₂(dppp) (340 mg, 0.576 mmol) and the reaction mixture were stirred at 50 °C for 12 h. After addition of water, organic layer was extracted with EtOAc, washed with brine, and dried over MgSO₄. After removing the solvent to c.a. 60 mL in vacuo, addition of MeOH and CHCl₃ afforded the titled compound (6.38 g, 9.45 mmol, 66%) as white solid, which was collected by filtration as a major part. In a mother liquor, there still remained small amount of the products. After removing the solvent in the mother liquor, the crude material was purified by silica gel column chromatography (hexane:chloroform = 80:20 to 50:50) to afford the titled compound (1.67 g, 2.47 mmol, 17%) as white solid. Total yield: 83%. M.p.: 167.3–167.9 °C. ¹H NMR (600 MHz, CDCl₃): δ 0.89 (t, J = 6.6 Hz, 6H, CH₃), 1.27–1.35 (m, 28H, (CH₂)₇), 1.69 (quin, J = 7.2 Hz, 4H, ArCH₂CH₂), 2.75 (t, J = 7.2 Hz, 4H, ArCH₂), 3.75 (s, 6H, OCH₃), 3.94 (s, 6H, OCH₃), 6.99 (s, 2H, ArH), 7.22 (s, 2H, ArH), 7.30 (d, J = 8.4 Hz, 2H, ArH), 7.56 (s, 2H, ArH), 7.70 (d, J = 8.4 Hz, 2H, ArH), 7.74 (s, 2H, ArH). ¹³C NMR (150 MHz, CDCl₃): δ 14.27, 22.84, 29.47, 29.49. 29.73, 29.77 (two carbons), 31.71. 32.05, 36.11, 55.85, 56.72, 105.51, 115.37, 126.32, 126.45, 127.82, 127.95, 128.95, 129.73, 130.20, 132.66, 138.39, 151.35, 155.51. HRMS (APCI+): Calcd for $C_{50}H_{67}O_4$ [M+H] 731.5039, found, 731.5031. Anal. Calcd for $C_{50}H_{66}O_4$: C, 82.15; H, 9.10. Found C, 82.27; H, 9.11.

2,5-bis(7-decyl-3-hydroxynaphthalen-2-yl)benzene-1,4-diol



To a suspension of 3,3'-(2,5-dimethoxy-1,4-phenylene)bis(6-decyl-2-methoxynaphthalene) (4.00 g, 5.47 mmol) in dichloromethane (22 mL) was added 1.0 M BBr₃ in dichloromethane (24.1 mL, 24.1 mmol, 4.4 mol amt.) at 0 °C and then was stirred at room temperature for 2 h. After the crude mixture was poured into ice water, organic layer was extracted with THF and EtOAc, washed with water and brine, and dried over MgSO₄. After removing the solvent to 30 mL in vacuo, addition of acetone and dichloromethane afforded the titled compound (2.83 g, 4.19 mmol, 77%) as white precipitate, which was collected by filtration as a major part. In a mother liquor, there still remained small amount of the products. After removing the solvent in the mother liquor, the crude material was purified by silica gel column chromatography (hexane:AcOEt = 90:10 to 75:25) to afford the titled compound (588 mg, 0.87 mmol, 16%) as white solid. Total yield: 93%. M.p.: 229.9-231.1 °C. ¹H NMR (400 MHz, THF- d_8): δ 0.89 (t, J = 6.8 Hz, 6H, CH₃), 1.26–1.42 (m, 28H, (CH₂)₇), 2.74 (t, J = 7.6 Hz, 4H, ArCH₂), 6.97 (s, 2H, ArH), 7.22 (s, 2H, ArH), 7.25 (d, J = 8.4 Hz, 2H, ArH), 7.56 (s, 2H, ArH), 7.60 (d, J = 8.4 Hz, 2H, ArH), 7.76 (s, 2H, ArH), 7.92 (s, 2H, OH), 8.41 (s, 2H, OH) 4 protons for ArCH₂CH₂ were overlapped with those of THF. 13 C NMR (150 MHz, THF- d_8): δ 15.04, 24.16, 30.88, 30.90, 31.15, 31.21 (two carbons), 33.09, 33.47, 37.39, 111.98, 120.90, 127.11, 127.56, 128.29, 128.82, 130.35, 130.67, 131.61, 134.51, 138.83, 149.30, 153.91. HRMS (APCI+): Calcd for C₄₆H₅₉O₄ [M+H] 675.4413, found, 675.4412. Anal. Calcd for C₄₆H₅₈O₄: C, 81.86; H, 8.66. Found C, 81.72; H, 8.58.

General procedure for dehydration reaction

2,10-Didecyldinaphtho[2,3-d:2',3'-d']benzo[1,2-b:4,5-b']difuran (C₁₀-DNBDF-NV)



To a white suspension of 2,5-bis(7-decyl-3-hydroxynaphthalen-2-yl)benzene-1,4-diol (810 mg, 1.20 mmol) in 1,2-dichlorobenzene (24 mL) was added Zeolite HSZ-360 (324 mg) and the reaction mixture was stirred at 160 °C for 20 h. The resultant mixture was passed through a short pad of Celite[®] to remove the Zeolite by hot filtration. After addition of MeOH to the filtrate, the formed precipitate was collected by filtration to afford the titled compound (579 mg, 0.91 mmol, 76%) as pale yellow solid. The obtained compound was purified by vacuum sublimation with diffusion pump (High temperature region: 330 °C, Low temperature region: 230 °C, pressure: ca. 10⁻³ Torr). M.p.: 313 °C (determined by DSC). ¹H NMR (600 MHz, CDCl₂CDCl₂, 100 °C): δ 0.88 (t, *J* = 7.2 Hz, 6H, CH₃), 1.26–1.43 (m, 28H, (CH₂)₇), 1.77 (quin, *J* = 7.8 Hz, 4H, ArCH₂CH₂), 2.82 (t, *J* = 7.8 Hz, 4H, ArCH₂), 7.39 (d, *J* = 8.4 Hz, 2H, ArH), 7.81 (s, 2H, ArH), 7.87 (d, *J* = 8.4 Hz, 2H, ArH), 7.89 (s, 2H, ArH), 8.13 (s, 2H, ArH), 8.38 (s, 2H, ArH). ¹³C NMR spectra could not be recorded due to the low solubility. HRMS (APCI+): Calcd for C₄₆H₅₅O₂ [M+H] 639.4202, found, 639.4199. Anal. Calcd for C₄₆H₅₄O₂: C, 86.47; H, 8.52. Found C, 86.56; H, 8.53.

Dinaphtho[2,3-d:2',3'-d']benzo[1,2-b:4,5-b']difuran (DNBDF)



Yield: 76%. The obtained compound was purified by vacuum sublimation with diffusion pump (High temperature region: 300 °C, Low temperature region: 170 °C, pressure: ca. 10⁻³ Torr). Pale yellow solid. M.p.: N.A. ¹H NMR (600 MHz, CDCl₂CDCl₂, 120 °C): δ 7.49 (dd, J = 8.4 Hz, 8.4 Hz, 2H, ArH), 7.53 (dd, J = 8.4 Hz, 8.4 Hz, 2H, ArH), 7.94 (s, 2H, ArH), 7.97 (d, J = 8.4 Hz, 2H, ArH), 8.05 (d, J = 8.4 Hz, 2H, ArH), 8.17 (s, 2H, ArH), 8.46 (s, 2H, ArH). ¹³C NMR spectra could not be recorded due to

the low solubility. HRMS (APCI+): Calcd for $C_{26}H_{15}O_2$ [M+H] 359.1072, found, 359.1067. Anal. Calcd for $C_{26}H_{14}O_2$: C, 87.13; H, 3.94. Found C, 87.15; H, 4.08.

3,11-Didecyldinaphtho[2,3-d:2',3'-d']benzo[1,2-b:4,5-b']difuran (C₁₀-DNBDF-NW)



Yield: 78%. The obtained compound was purified by vacuum sublimation with diffusion pump (High temperature region: 330 °C, Low temperature region: 230 °C, pressure: ca. 10^{-3} Torr). Pale yellow solid. M.p.: 371 °C (determined by DSC). ¹H NMR (600 MHz, CDCl₂CDCl₂ at 100 °C): δ 0.89 (t, J = 6.6 Hz, 6H, CH_3), 1.25–1.44 (m, 28H, (CH_2)₇), 1.78 (quin, J = 7.2 Hz, 4H, ArCH₂CH₂), 2.83 (t, J = 7.2 Hz, 4H, ArCH₂), 7.34 (d, J = 8.4 Hz, 2H, ArH), 7.72 (s, 2H, ArH), 7.86 (s, 2H, ArH), 7.95 (d, J = 8.4 Hz, 2H, ArH), 8.12 (s, 2H, ArH), 8.40 (s, 2H, ArH). ¹³C NMR spectra could not be recorded due to the low solubility. HRMS (APCI+): Calcd for C₄₆H₅₅O₂ [M+H] 639.4202, found, 639.4197. Anal. Calcd for C₄₆H₅₄O₂: C, 86.47; H, 8.52. Found C, 86.63; H, 8.14.

2. Absorption Spectra in Evaporated Thin Film

UV-vis absorption spectra were measured with a JASCO V-570 spectrometer. Thin films were prepared by vacuum deposition with the thickness of 100 nm on quartz substrates. **DNBDF** derivatives in solution were prepared in degassed 1,2-dichlorobenzene.



Figure S1. Absorption spectra of **DNBDF** derivatives and **DNF–V** (**DNBDF**: blue, C₁₀–**DNBDF–NW**: red, C₁₀–**DNBDF–NV**: green, **DNF–V**: black) in vacuum deposited thin films on quartz substrate.

3. Fluorescent Spectra

Photoluminescence spectra and absolute quantum yields were recorded with a Hamamatsu Photonics C9920–02 Absolute PL Quantum Yield Measurement System. The samples in solution were prepared in degassed 1,2-dichlorobenzene.



Figure S2. Fluorescent spectra of **DNBDF** derivatives and **DNF–V** (**DNBDF**: blue, C₁₀–**DNBDF–NW**: red, C₁₀–**DNBDF–NV**: green, **DNF–V**: black) in solid state.



Figure S3. Fluorescent spectra of **DNBDF** derivatives in 1,2-dichlorobenzene solution and **DNF–V** in 1,2-dichloroethane. (**DNBDF**: blue, C_{10} –**DNBDF–NW**: red, C_{10} –**DNBDF–NW**: red, C_{10} –**DNBDF–NV**: green, **DNF–V**: black)

Table S1. Summarized optical properties of DNF–V, DNBDF, C₁₀–DNBDF–NW, and C₁₀–DNBDF–NV

	UV/Vis absorption	Fluorescence in solution		Fluorescence in solid state	
Compound	$\lambda_{\max} (\mathrm{nm})^a$	$\lambda_{\max} (\mathrm{nm})^b$	$\Phi(ext{solu.})$	$\lambda_{ ext{max}} \ (ext{nm})^c$	$\Phi(ext{solid})$
$\mathbf{DNF}-\mathbf{V}^{d}$	322, 337, 362, 382	389, 410, 431 (sh)	0.83	408 (sh), 427, 455, 488, 524	0.72
DNBDF	295, 346, 362, 394	400, 422, 446 (sh)	0.65	444, 468, 500, 536	0.71
C ₁₀ -DBDNF-NW	294, 349, 367, 396	408, 425, 452 (sh)	0.78	441, 465, 497. 535 (sh)	0.36
C ₁₀ -DNBDF-NV	294, 349, 367, 397	402, 424, 450 (sh)	0.69	441, 461, 491, 527 (sh)	0.42

^{*a*} Wavelength of absorption intensity maximum in 1,2-dichlorobenzene. ^{*b*} Wavelength of emission intensity maximum in 1,2-dichlorobenzene. ^{*c*} Wavelength of emission intensity in solid state. ^{*d*} Measured in 1,2-dichlorobenzene.

4. Ionization Potentials

Photoelectron yield spectroscopy (PYS) was performed on a Sumitomo Heavy Industries Advanced Machinery PYS-202. For PYS measurements, thin films (*ca.* 100 nm) of **DNBDF** derivatives were thermally evaporated on ITO coated quartz substrates and measurements were performed in vacuum. The photoelectron yield spectra are depicted in Figure S4.



Figure S4. Photoelectron yield spectra of **DNBDF** derivatives in thin films after light illumination from a D_2 lamp *in vacuo*.

5. Thermal Analyses

5.1 Thermogravimetric Analyses (TGA)

TGA measurements were carried out with a Rigaku Thermo Plus EVO II TG 8120. Sample was placed in aluminum pan and heated at the rate of 5 K/min, under N_2 purge at a flow rate of 100 mL/min. Al₂O₃ was used as reference material.



Figure S5. TGA charts of DNBDF derivatives.

5.2 Differential Scanning Calorimetric (DSC) Analyses

DSC measurements were carried out with a Rigaku Thermo Plus EVO II DSC8270. Sample was placed in aluminum pan and heated at the rate of 5 K/min, under N_2 purge at a flow rate of 100 mL/min. Al₂O₃ was used as reference material.



Figure S6. DSC charts of C₁₀–DNBDF–NW (red line) and C₁₀–DNBDF–NV (green line).

6. Single-Crystal Analyses

We have obtained the single crystals of **DNBDF** by physical vapor transport technique. Single crystals of C_{10} -**DNBDF**-**NV** and C_{10} -**DNBDF**-**NW** were prepared by means of recrystallization from a mixture of 1,2-dimethoxybenzene. Single crystal diffraction data were collected on a Rigaku R-AXIS RAPID II imaging plate diffractometer with CuK α radiation.

Crystal data for **DNBDF**: C₂₆H₂₂O₂, M = 366.46, a colorless plate, $0.623 \times 0.454 \times 0.01$ mm, triclinic, P-1, a = 5.946(3), b = 7.516(4), c = 18.704(10), Å, $\alpha = 96.63(2)^{\circ}$, $\beta = 91.21(2)^{\circ}$, $\gamma = 90.083(18)^{\circ}$, V = 830.1(7) Å³, Z = 2, $\rho_{calcd} = 1.466$ g cm⁻³, T = 296 K, $2\theta_{max} = 128.1^{\circ}$, CuK α radiation, $\lambda = 1.54187$ Å, $\mu = 0.714$ mm⁻¹, 9927 reflections measured, 2926 unique reflections, $R_{int} = 16.28\%$, 253 parameters, $R_1 = 0.2121$ ($I > 2\sigma(I)$), $wR_2 = 0.5037$ (all data), CCDC–1400150.

Crystal data for C₁₀–DNBDF–NW: C₄₆H₅₄O₂, M = 638.93, a colorless plate, 0.523 × 0.302 × 0.005 mm, orthorhombic, *Pbca*, a = 7.3950(5), b = 5.8775(4), c = 80.760(6) Å, V = 3510.2(4) Å³, Z = 4, $\rho_{calcd} = 1.209$ g cm⁻³, T = 296 K, $2\theta_{max} = 136.5^{\circ}$, Cu*Ka* radiation, $\lambda = 1.54187$ Å, $\mu = 0.545$ mm⁻¹, 36598 reflections measured, 3204 unique reflections, $R_{int} = 19.86\%$, 217 parameters, $R_1 = 0.1178$ ($I > 2\sigma(I)$), $wR_2 = 0.3051$ (all data), CCDC–1400149.

Crystal data for C_{10} -DNBDF-NV: $C_{46}H_{54}O_2$, M = 638.93, a colorless plate, 0.332 × 0.165 × 0.005 mm, monoclinic, $P2_1/c$, a = 41.774(10), b = 7.4659(17), c = 5.9023(13) Å, $\beta = 93.859(7)^\circ$, V = 1836.6(7) Å³, Z = 2, $\rho_{calcd} = 1.155$ g cm⁻³, T = 296 K, $2\theta_{max} = 134.3^\circ$, CuK α radiation, $\lambda = 1.54187$ Å, $\mu = 0.521$ mm⁻¹, 7636 reflections measured, 1335 unique reflections, $R_{int} = 16.57\%$, 218 parameters, $R_1 = 0.1540$ ($I > 2\sigma(I)$), $wR_2 = 0.4401$ (all data), CCDC-1400151.

7. Theoretical Calculations

Frontier molecular orbitals and energy levels of **DNF–V** and **DNBDF** derivatives were calculated for a single molecule at the B3LYP/6-31G* level.



Figure S7. HOMO and LUMO of **DNF–V** and **DNBDF**.

Electronic band structure calculations were conducted based on the packing structure by way of 2-dimensional periodic boundary condition at the PBEPBE/6-31G(d) level. The energies are plotted and labeled as $\Gamma = (0, 0, 0), S = (0.5, 0.5, 0), T = (0, 0.5, 0.5), U = (0.5, 0, 0.5), X = (0.5, 0, 0), Y = (0, 0.5, 0), Z = (0, 0, 0.5)$ in the crystallographic coordinates. Effective hole masses were calculated as $m^* = \hbar^2 \left(\frac{\partial^2 E(k)}{\partial k^2}\right)^{-1}$ along respective directions.



Figure S8. Electronic band structure of **DNBDF** crystal (*a-b* plane). Left axis is the energy relative to the top of the valence band.



Figure S9. Electronic band structure of C_{10} -DNBDF-NW crystal (*a-b* plane). Left axis is the energy relative to the top of the valence band.



Figure S10. Electronic band structure of C_{10} -DNBDF-NV crystal (*b*-*c* plane). Left axis is the energy relative to the top of the valence band.



Figure S11. Electronic band structure of C_{10} -DNF-VW crystal (*a*-*c* plane). Left axis is the energy relative to the top of the valence band.

8. OFET Device Fabrication and Evaluation Procedure

The surface of the substrates with 500-nm-thick thermally oxidized SiO₂ on doped Si is first sonificated in acetone and 2-propanol for each 5 min, followed by UV-ozone exposure for 30 min. The surface of the cleaned substrates is treated with β -phenylethyltrichlorosilane (β -PTS) in toluene solution. To form the crystalline thin films, a 0.05 wt% solution of C₁₀-DNBDF-NV in 1,2,4-trichlorobenzene dissolved at 120 °C is dropped at an edge of a sustaining structure on a heated substrate at 90 °C and the crystalline domains grow in the direction of evaporation of the solvent. The structure to support the droplet can be removed after the growth of the crystalline film. Then, F₄-TCNQ (thickness: 1–2 nm) and the Au electrodes (thickness: 40 nm) are evaporated on the C₁₀-DNBDF-NV film through a shadow mask. The doped-Si layer acts as a gate electrode and SiO₂ layer as a dielectrics with relative permittivity of 3.9. A schematic illustration of FET is given in Figure S12. Electrical characterization was performed in ambient condition using a semiconductor parameter analyzer (Keithley 4200). Field-effect mobility (μ_{FET}) values were estimated from the saturation regime using the following equation:

$$I_{\rm D} = (WC_{\rm i}/2L)\mu_{\rm FET}(V_{\rm G}-V_{\rm th})^2,$$

where μ_{FET} is the carrier mobility in saturated region, W is the channel width, L is the channel length, I_{D} is the drain current, V_{G} is the gate voltage, C_{i} is the capacitance of gate insulator and V_{th} is the threshold voltage.

Representative 5 device performances are depicted in Figure S14–18.



Figure S12. (a) Schematic image of the crystalline thin film formation by edge-cast method. (b) Schematic device structure based on C_{10} -DNBDF-NV.



Figure S13. OFET characters of C_{10} -DNBDF-NV (Device 1). Transfer (left)- and output (right) characteristics (L/W = 100/60, SiO₂: 500 nm).



Figure S14. OFET characters of C_{10} -DNBDF-NV (Device 2). Transfer (left)- and output (right) characteristics (L/W = 100/113, SiO₂: 500 nm).



Figure S15. OFET characters of C_{10} -DNBDF-NV (Device 3). Transfer (left)- and output (right) characteristics (L/W = 100/69, SiO₂: 500 nm).



Figure S16. OFET characters of C_{10} -DNBDF-NV (Device 4). Transfer (left)- and output (right) characteristics (L/W = 100/56, SiO₂: 500 nm).



Figure S17. OFET characters of C_{10} -DNBDF-NV (Device 5). Transfer (left)- and output (right) characteristics (L/W = 100/62, SiO₂: 500 nm).

9. X-ray-diffraction Measurements for Solution-crystallized Thin Film

The X-ray-diffraction measurements were performed using Rigaku Mercury 70 with $CuK\alpha$ radiation.



Figure S18. The Laue spots of the solution-crystalized C_{10} -DNBDF-NV thin film on the imaging plate in the (a) in-plane and (b) out-of-plane measurements.



10. Photograph of solution-crystallized thin film of C_{10} -DNBDF-NV

Figure S19. Representative photo of solution-crystallized thin film of C_{10} -DNBDF-NV.

11. References

(1) K. Niimi, M. J. Kang, E. Miyazaki, I. Osaka, K. Takimiya, Org. Lett., 2011, 13, 3430–3433.

(2) C. Mitsui, T. Okamoto, M. Yamagishi, J. Tsurumi, K. Yoshimoto, K. Nakahara, J. Soeda, Y. Hirose, H. Sato, A. Yamano, T. Uemura, J. Takeya, *Adv. Mater.*, 2014, **26**, 4546–4551.